Ordering number : ENN6293A

Schottky Barrier Diode

SBE802

100V, 400mA Rectifier

Applications

- High frequency rectification (switching regulators, converters, and choppers).

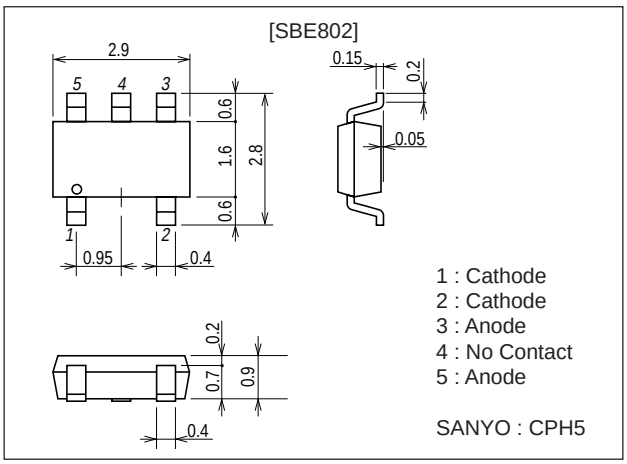
Features

- Low forward voltage (V_F max=0.7V).
- Fast reverse recovery time (t_{rr} max=10ns).
- Low switching noise.
- Low leakage current and high reliability due to highly reliable planar structure.

Package Dimensions

unit : mm

1294



Specifications

Absolute Maximum Ratings at Ta=25°C (Value per element)

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		100	V
Nonrepetitive Peak Reverse Surge Voltage	V_{RSM}		100	V
Average Output Current	I_O		400	mA
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	5	A
Junction Temperature	Tj		−55 to +125	°C
Storage Temperature	Tstg		−55 to +125	°C

Electrical Characteristics at Ta=25°C (Value per element)

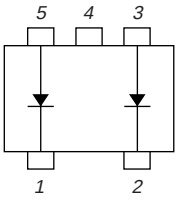
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Reverse Voltage	V_R	I_R=200μA	100			V
Forward Voltage	V_F	I_F=200mA		0.5	0.55	V
		I_F=400mA			0.7	V
Reverse Current	I_R	V_R=45V			50	μA
Interterminal Capacitance	C	V_R=10V, f=1MHz		20		pF
Reverse Recovery Time	t_{rr}	I_F=I_R=100mA, See specified Test Circuit.			10	ns
Thermal Resistance	Rth(j-a)	Mounted on a ceramic board (600mm²×0.8mm)			110	°C/W

Marking : SA

SANYO Electric Co.,Ltd. Semiconductor Company

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Electrical Connection



1 : Cathode
2 : Cathode
3 : Anode
4 : No Contact
5 : Anode

t_{rr} Test Circuit